

# Phase Control Dual SCR, SCR/Diode Modules

Replaces December 1998 version, DS4482-5.0

DS4482-6.0 January 2000

#### **FEATURES**

- Dual Device Module
- Electrically Isolated Package
- Pressure Contact Construction
- International Standard Footprint
- Alumina (non-toxic) Isolation Medium

#### **APPLICATIONS**

- Motor Control
- Controlled Rectifier Bridges
- Heater Control
- AC Phase Control

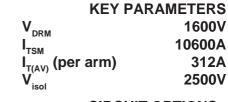
#### **VOLTAGE RATINGS**

Type Number	Repetitive Peak Voltages V <sub>DRM</sub> V <sub>RRM</sub>	Conditions
MP03/300 - 16	1600	T <sub>(vj)</sub> = 125°C
MP03/300 - 14	1400	$I_{DRM} = I_{RRM} = 30 \text{mA}$
MP03/300 - 12	1200	V <sub>DSM</sub> & V <sub>RSM</sub> = V <sub>DRM</sub> & V <sub>RRM</sub> + 100V
MP03/300 - 10	1000	respectively

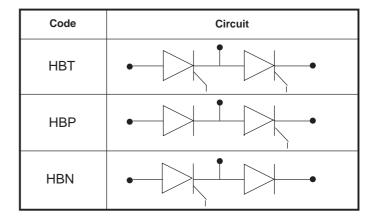
Lower voltage grades available.

For full description of part number see "Ordering instructions" on page 3.

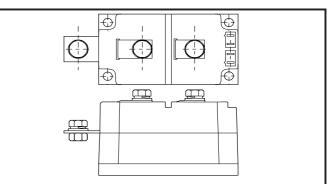
#### **CURRENT RATINGS - PER ARM**



#### **CIRCUIT OPTIONS**



#### PACKAGE OUTLINE



#### Module type code: MP03. See Package Details for further information

Symbol	Parameter	Conditions		Max.	Units
			T <sub>case</sub> = 75°C	312	А
			$T_{case} = 85^{\circ}C$	265	А
I <sub>T(AV)</sub> Mean on-state current	Mean on-state current	Halfwave, resistive load	T <sub>heatsink</sub> = 75°C	216	А
			T <sub>heatsink</sub> = 85°C	181	А
I <sub>T(RMS)</sub>	RMS value	$T_{case} = 75^{\circ}C$		490	А

## SURGE RATINGS - PER ARM

Symbol	Parameter	Conditions		Max.	Units
I <sub>FSM</sub> Surge (non-repetitive) on-state current	10ms half sine;	V <sub>R</sub> = 0	10.6	kA	
	Surge (non-repetitive) on-state current		$V_{R} = 50\% V_{RRM}$	8.5	kA
124	I <sup>2</sup> t I <sup>2</sup> t for fusing	10ms half sine; T <sub>j</sub> = 125°C	V <sub>R</sub> = 0	0.56 x 10 <sup>6</sup>	A <sup>2</sup> s
1-t			$V_{R} = 50\% V_{RRM}$	0.36 x 10 <sup>6</sup>	A <sup>2</sup> s

#### **THERMAL & MECHANICAL RATINGS**

Symbol	Parameter	Conditions	Max.	Units
		dc	0.11	°C/W
R <sub>th(j-c)</sub>	R <sub>th(j-c)</sub> Thermal resistance - junction to case per Thyristor or Diode	halfwave	0.12	°C/W
		3 phase	0.13	°C/W
R <sub>th(c-hs)</sub>	Thermal resistance - case to heatsink per thyristor or diode	Mounting torque = 5Nm with mounting compound	0.05	°C/W
T <sub>vj</sub>	Virtual junction temperature	Off-state (Blocking)	125	°C
T <sub>stg</sub>	Storage temperature range		-40 to 125	°C
V <sub>isol</sub>	Isolation voltage	Commoned terminals to base plate AC RMS, 1min, 50Hz	2.5	kV

## **DYNAMIC CHARACTERISTICS- THYRISTOR**

Symbol	Parameter	Conditions	Max.	Units
V <sub>TM</sub>	On-state voltage	At 1000A, T <sub>case</sub> = 25°C - See Note 1	1.50	V
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At $V_{RRM}/V_{DRM}$ , $T_j = 125^{\circ}C$	30	mA
dV/dt	Linear rate of rise of off-state voltage	To 67% V <sub>DRM</sub> T <sub>j</sub> = 125°C	200*	V/µs
dl/dt	Rate of rise of on-state current	From 67% $V_{DRM}$ to 600A Gate source 10V, 5 $\Omega$ Rise time 0.5µs, T <sub>j</sub> =125°C	100	A/μs
V <sub>T(TO)</sub>	Threshold voltage	At T <sub>vj</sub> = 125°C - See Note 1	0.8	V
r <sub>⊤</sub>	On-state slope resistance	At T <sub>vj</sub> = 125°C - See Note 1	0.7	mΩ

\* Higher dV/dt values available, contact factory for particular requirements.

Note 1: The data given in this datasheet with regard to forward voltage drop is for calculation of the power dissipation in the semiconductor elements only. Forward voltage drops measured at the power terminals of the module will be in excess of these figures due to the impedance of the busbar from the terminal to the semiconductor.

Symbol	Parameter	Conditions		Max.	Units
V <sub>gt</sub>	Gate trigger voltage	$V_{\text{DRM}} = 5V, T_{\text{case}} = 25^{\circ}\text{C}$	-	3.0	V
Ι <sub>gτ</sub>	Gate trigger current	$V_{\text{DRM}} = 5V, T_{\text{case}} = 25^{\circ}\text{C}$	-	150	mA
V <sub>gd</sub>	Gate non-trigger voltage	At $V_{\text{DRM}} T_{\text{case}} = 25^{\circ}\text{C}$	-	0.25	V
V <sub>FGM</sub>	Peak forward gate voltage	Anode positive with respect to cathode	-	30	V
V <sub>FGN</sub>	Peak forward gate voltage	Anode negative with respect to cathode	-	0.25	V
V <sub>RGM</sub>	Peak reverse gate voltage		-	5.0	V
I <sub>FGM</sub>	Peak forward gate current	Anode positive with respect to cathode	-	10	А
Р <sub>бм</sub>	Peak gate power	t <sub>p</sub> = 25μs	-	100	W
P <sub>G(AV)</sub>	Mean gate power		-	5	W

#### GATE TRIGGER CHARACTERISTICS AND RATINGS

#### **ORDERING INSTRUCTIONS**

Part number is made up of as follows:

MP03 HBT 300 -12

MP = Pressure contact module

03 = Outline type

HBT = Circuit configuration code (see "circuit options" - front page)

- 300 = Nominal average current rating at  $T_{case} = 75^{\circ}C$
- $12 = V_{RRM}/100$

NOTE: Diode ratings and characteristics are comparable with the SCR in types HBP or HBN Types HBP or HBN can also be supplied with diode polarity reversed, to special order.

#### MOUNTING RECOMMENDATIONS

■ Adequate heatsinking is required to maintain the base temperature at 75°C if full rated current is to be achieved. Power dissipation may be calculated by use of  $V_{T(TO)}$  and  $r_{T}$  information in accordance with standard formulae. We can provide assistance with calculations or choice of heatsink if required.

The heatsink surface must be smooth and flat; a surface finish of N6 ( $32\mu$ in) and a flatness within 0.05mm (0.002") are recommended.

■ Immediately prior to mounting, the heatsink surface should be lightly scrubbed with fine emery of Scotch Brite or a mild chemical etchant and then cleaned with a solvent to remove oxide build up and foreign material. Care should be taken to ensure no foreign particles remain.

■ An even coating of thermal compound (eg. Unial) should be applied to both the heatsink and module mounting surfaces. This should ideally be 0.05mm (0.002") per surface to ensure optimum thermal performance.

■ After application of thermal compound, place the module squarely over the mounting holes, (or 'T' slots) in the heatsink. Using a torque wrench, slowly tighten the recommended fixing bolts at each end, rotating each in turn no more than 1/4 of a revolution at a time. Continue until the required torque of 5Nm (44lb.ins) is reached at both ends.

■ It is not acceptable to fully tighten one fixing bolt before starting to tighten the others. Such action may DAMAGE the module.

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Examples:

MP03 HBP300 - 16 MP03 HBN300 - 10 MP03 HBT300 - 14

#### **CURVES**

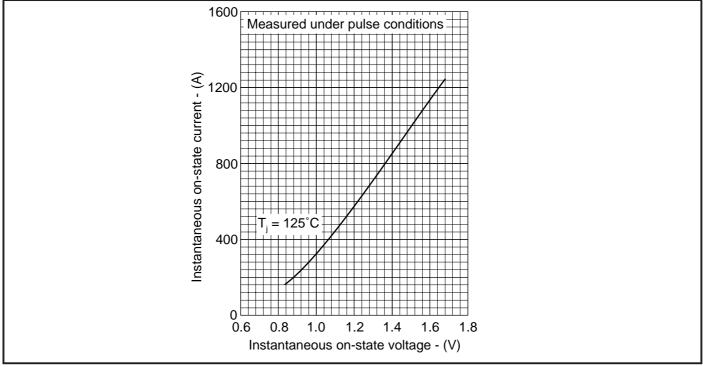


Fig. 1 Maximum (limit) on-state characteristics (thyristor or diode) - See Note 1

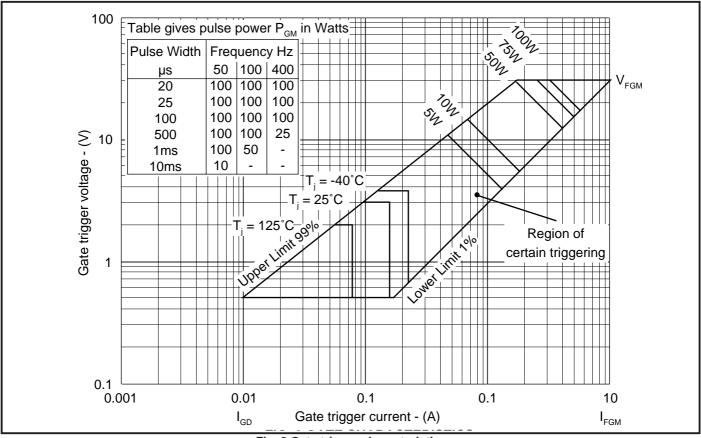


Fig. 2 Gate trigger characteristics

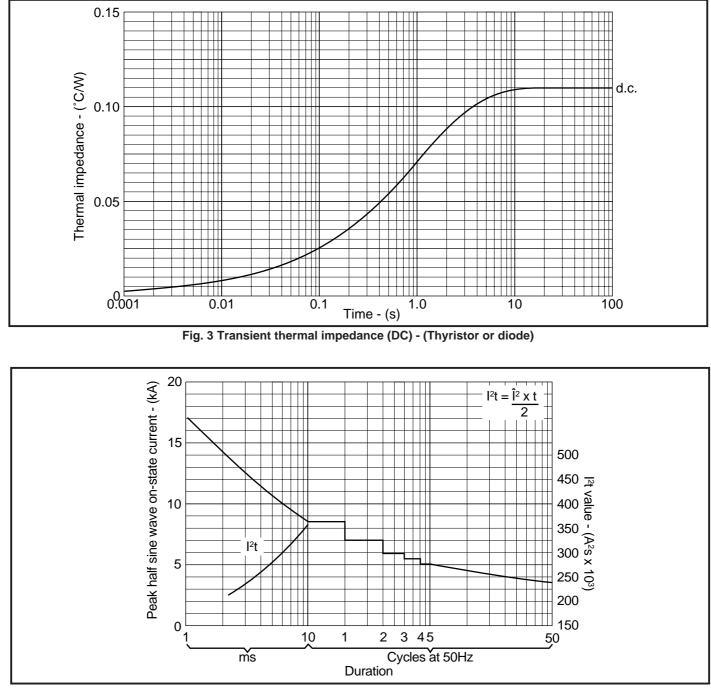


Fig. 4 Surge (non-repetitive) on-state current vs time (with 50% V<sub>RRM</sub>, T<sub>case</sub> = 125°C (Thyristor or diode)

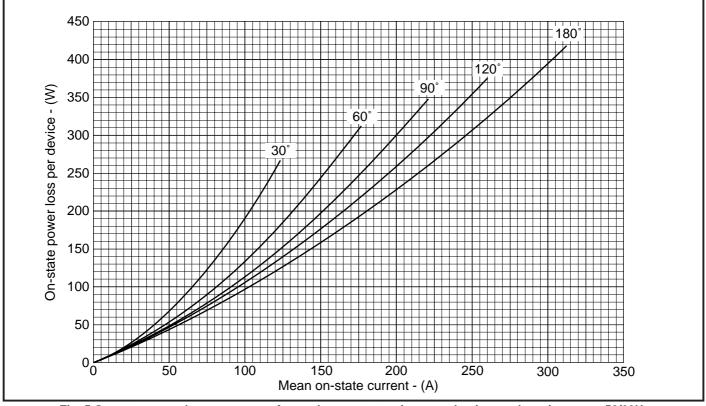


Fig. 5 On-state power loss per arm vs forward current at various conduction angles, sine wave, 50/60Hz

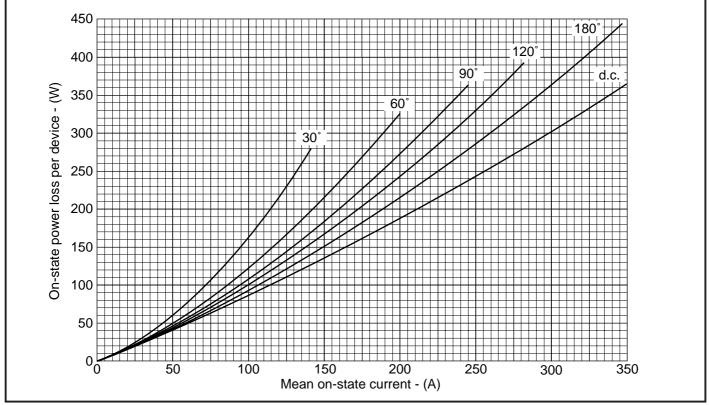


Fig. 6 On-state power loss per arm vs forward current at various conduction angles, square wave, 50/60Hz

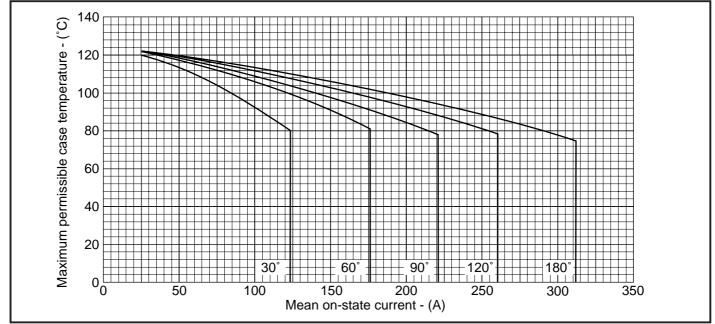


Fig. 7 Maximum permissible case temperature vs forward current per arm at various conduction angles, sine wave, 50/60Hz

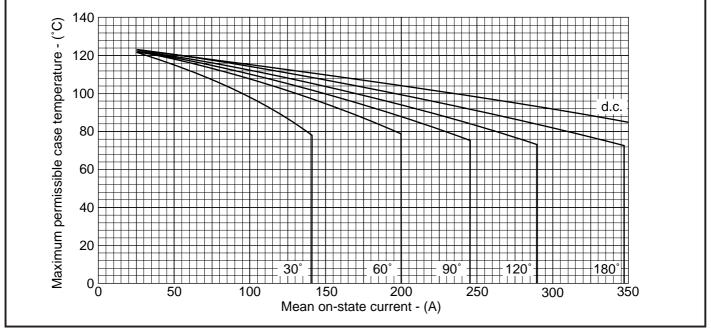


Fig. 8 Maximum permissible case temperature vs forward current per arm at various conduction angles, square wave, 50/60Hz

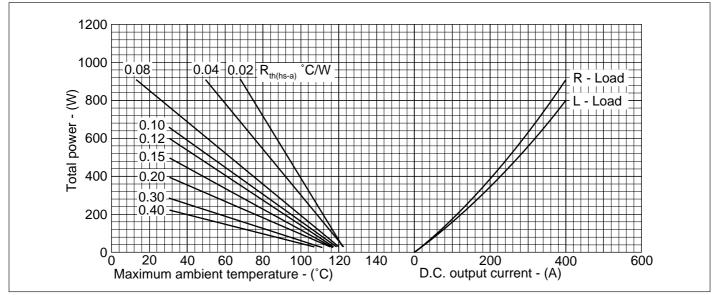


Fig. 9 50/60Hz single phase bridge dc output current vs power loss and maximum permissible ambient temperature for various values of heatsink thermal resistance.

(Note: R<sub>th(hs-a)</sub> values given above are true heatsink thermal resistances to ambient and already account for R<sub>th(c-hs)</sub> module contact thermal).

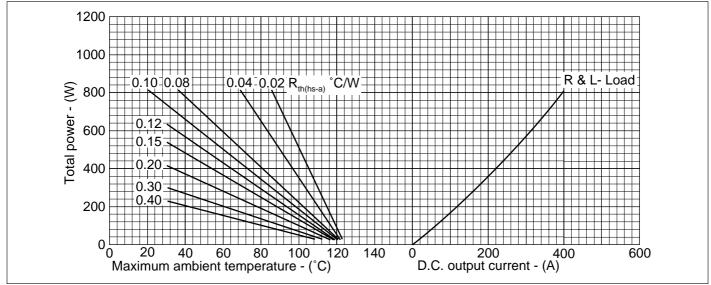
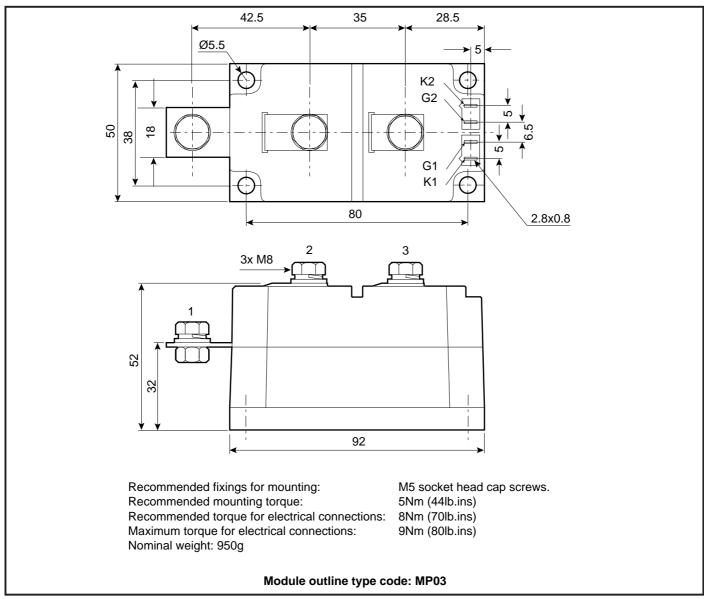


Fig. 9 50/60Hz 3- phase bridge dc output current vs power loss and maximum permissible ambient temperature for various values of heatsink thermal resistance.

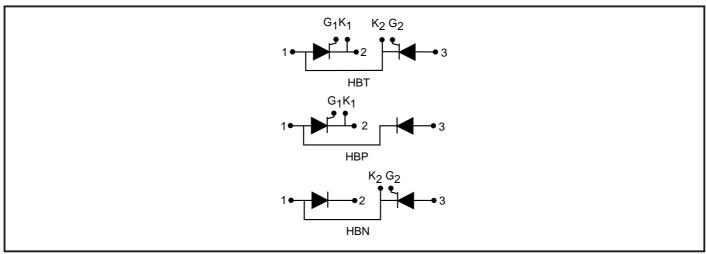
(Note: R<sub>th(ths-a)</sub> values given above are true heatsink thermal resistances to ambient and already account for R<sub>th(c-hs)</sub> module contact thermal).

## PACKAGE DETAILS

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



## CIRCUIT CONFIGURATIONS





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No Annotation: The product parameters are fixed and the product is available to datasheet specification.

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